

Plasma field effect transistors arrays for amplitude and polarization imaging in THz range

Knap Wojciech^{1,2}, Moulin Benoit³, Sypek M.⁴, Coquillat D.¹, Cywinski G.², Suszek J.¹, Triki M.¹, But D.¹, Siemion A.¹, Szkudlarek K.³, Archier C.³, Diakonova N.¹, Antonini T.³, Teppe Frédéric¹

¹ University of Montpellier,

² Polish Academy of Sciences,

³ T-Waves Technologies Montpellier,

⁴ Warsaw University of Technology

Materials Science and Condensed Matter Physics

Nr. 3(4) / 2005 / ISSN 1810-648X / ISSNe 2537-6365

Disponibil online 18 July, 2019. Descarcări-5. Vizualizări-730

Physics of nanometer plasma field effect transistors for detection of terahertz radiation

Knap Wojciech , But D., Diakonova N., Teppe Frédéric, Coquillat D.

University of Montpellier

Materials Science and Condensed Matter Physics

Nr. 3(21) / 2005 / ISSN 1810-9551

Disponibil online 24 February, 2019. Descarcări-1. Vizualizări-602

III-V versus silicon choice of nanometer field effect transistors for THz applications

Knap Wojciech , But D., Coquillat D., Diakonova N., Teppe Frédéric

University of Montpellier

Materials Science and Condensed Matter Physics

Nr. 2(17) / 2006 / ISSN 1810-1852 / ISSNe 1810-1879

Disponibil online 5 March, 2020. Descarcări-0. Vizualizări-644

Silicon versus III-V semiconductor material choice for terahertz imaging with nanometer field effect transistors based detectors

Knap Wojciech , Coquillat D., Diakonova N., Teppe Frédéric

Université Montpellier II

Materials Science and Condensed Matter Physics

Nr. 16(29) / 2012 / ISSN 1857-0054

Disponibil online 12 April, 2021. Descarcări-0. Vizualizări-329
